

Gusnu K Azhdarov

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Modeling the distribution of Ga and Sb impurities in Ge ^{1-x} Si single crystals grown by double feeding of the melt: Growth conditions for homogeneous single crystals. Crystallography Reports, 2016, 61, 327-330.	0.6	3
2	Modeling the concentration profiles of aluminum and indium impurities in crystals of germanium-silicon solid solutions. Inorganic Materials, 2016, 52, 244-247.	0.8	2
3	Deep acceptor complex in thermally processed Ge-Si ^{1-x} Ge ₂ Se ₃ crystals. Crystallography Reports, 2014, 59, 563-566.	0.6	0
4	Hybrid technique for growing homogeneous single crystals of semiconductor solid solutions from melt. Crystallography Reports, 2014, 59, 442-445.	0.6	4
5	Distribution of Al and in impurities along homogeneous Ge-Si crystals grown by the Czochralski method using Si feeding rod. Crystallography Reports, 2014, 59, 415-417.	0.6	0
6	Growth dynamics of Ge ^{1-x} Si ^x single crystals obtained by directional constitutional supercooling of the melt. Crystallography Reports, 2011, 56, 531-534.	0.6	1
7	Electroactive complex in thermally treated Ge-Si ^{1-x} Ge ₂ Se ₃ crystals. Crystallography Reports, 2010, 55, 462-465.	0.6	2
8	Growth of single crystals of semiconductor solid solutions by double feeding of the melt method. Crystallography Reports, 2010, 55, 716-719.	0.6	9
9	Deep donor center in Ge ^{1-x} Si ^x Ge ₂ Se ₃ crystals at 1050-1080 K. Inorganic Materials, 2010, 46, 1285-1289.	0.8	2
10	The distribution of Ga and Sb impurities in Ge-Si crystals grown by the Bridgman method using a feeding rod. Crystallography Reports, 2009, 54, 152-156.	0.6	8
11	Segregation of aluminum and indium impurities in Ge ^{1-x} Si ^x crystals. Inorganic Materials, 2007, 43, 3-7.	0.8	11
12	Distribution of aluminum and indium impurities in crystals of Ge-Si solid solutions grown from the melt. Crystallography Reports, 2006, 51, S192-S195.	0.6	12
13	Growth of homogeneous single crystals of GeSi solid solutions using a Ge seed by the modified Bridgman method. Crystallography Reports, 2005, 50, S149-S151.	0.6	4
14	Distribution of components in Ge-Si bulk single crystals grown under the continuous feeding of the melt with the second component (Si). Journal of Crystal Growth, 2001, 226, 437-442.	1.5	24
15	Deep impurity levels in Ge ^{1-x} Si ^x alloys. Solid State Communications, 1999, 111, 675-679.	1.9	4
16	Electron mobility in Ge-like Ge-Si alloys. Solid State Communications, 1992, 84, 445-447.	1.9	2
17	Negative Magnetoresistance in Indium Arsenide in the Extreme Quantum Limit. Physica Status Solidi (B): Basic Research, 1978, 87, 163-167.	1.5	3